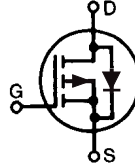


Standard Power MOSFET

P-Channel Enhancement Mode
Avalanche Rated

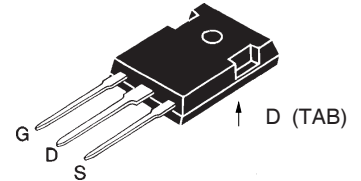
IXTH 8P50
IXTT 8P50

$$\begin{aligned} V_{DSS} &= -500 \text{ V} \\ I_{D25} &= -8 \text{ A} \\ R_{DS(on)} &= 1.2 \Omega \end{aligned}$$

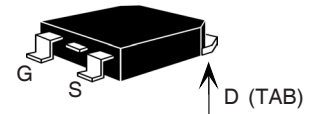


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	-500	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	-500	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	-8	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_J	-32	A
I_{AR}	$T_C = 25^\circ\text{C}$	-8	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
P_D	$T_C = 25^\circ\text{C}$	180	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
	Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
	Plastic Body for 10s	250	$^\circ\text{C}$
M_d	Mounting torque (TO-247)	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	5	g

TO-247 (IXTH)



TO-268 (IXTT)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance (<5 nH)
- easy to drive and to protect

Applications

- High side switching
- Push-pull amplifiers
- DC choppers
- Automatic test equipment

Advantages

- Easy to mount with 1 screw
(isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = -250 \mu\text{A}$ BV_{DSS} Temperature Coefficient	-500	0.054	V %/K
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \mu\text{A}$ $V_{GS(th)}$ Temperature Coefficient	-3.0	-0.122	V %/K
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0 \text{ V}$, $T_J = 125^\circ\text{C}$			-200 μA -1 mA
$R_{DS(on)}$	$V_{GS} = -10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ $R_{DS(on)}$ Temperature Coefficient			1.5 Ω 1.2 Ω 0.6 %/K

